

In the Claims:

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11 (previously added). A component, which comprises:

a substrate;

a lower insulating layer having a layer thickness between 0.05  $\mu\text{m}$  and 50  $\mu\text{m}$  and having a region;

at least one upper insulating layer having a layer thickness between 0.05  $\mu\text{m}$  and 50  $\mu\text{m}$  and having a region; and

at least one activated region that is activated for a process selected from the group consisting of subsequent metallization, photosensitization, hydrophobicization and surface functionalization that is other than metallization, photosensitization, and hydrophobicization;

said at least one activated region being selected from the group consisting of said region of said lower insulating layer and said region of said at least one upper insulating layer;

said lower insulation layer located adjacent said at least one upper insulation layer.

12 (previously added). The component according to claim 11, wherein said substrate, said lower insulating layer, and said at least one upper insulating layer form a component selected from the group consisting of an electronic component and a microelectronic component.

13 (previously added). The component according to claim 11, wherein said lower insulating layer is chemically different from said at least one upper insulating layer.

F 14 (previously added). The component according to claim 11, wherein said at least one said upper layer is a layer selected from the group consisting of a patterned layer and a mask layer for activating said lower layer.

15 (previously added). The component according to claim 11, wherein said at least one activated region is a region selected from the group consisting of a seeded region and a metallized region.

16 (previously added). A process for producing a component, which comprises:

in a first working step, applying a lower insulating layer to a substrate;

in a second working step, activating at least one region of the lower insulating layer; and

in a third working step, applying at least one upper insulating layer to the lower, activated insulating layer and patterning the at least one upper insulating layer.

17 (previously added). The process according to claim 16, which comprises patterning the lower insulating layer in the first working step.

F 18 (previously added). The process according to claim 16, which comprises choosing a selected layer from the group consisting of the at least upper one insulating layer and the lower insulating layer and patterning the selected layer after the selected layer has been applied.

19 (previously added). A process for producing a component, which comprises:

in a first working step, applying a first insulating layer to a substrate;

in a second working step, applying a second insulating layer and patterning the second insulating layer; and

in a third working step, activating a layer selected from the group consisting of the first insulating layer and the second insulating layer.

20 (previously added). The process according to claim 19, which comprises patterning the first insulating layer in the first working step.

21 (previously added). The process according to claim 19, which comprises patterning the second insulating layer after the second working step and before the third working step.

22 (previously added). The process according to claim 21, which comprises patterning the lower insulating layer, after the first working step.

23 (previously added). The process according to claim 19, which comprises patterning the lower insulating layer, after the first working step.

24 (previously added). A process for producing a component, which comprises:

in a first working step, applying a lower insulating layer having a layer thickness between 0.05  $\mu\text{m}$  and 50  $\mu\text{m}$  to a substrate;

in a second working step, activating at least one region of the lower insulating layer; and

in a third working step, applying at least one upper insulating layer having a layer thickness between 0.05  $\mu\text{m}$  and 50  $\mu\text{m}$  and being chemically different from said at least one lower insulating layer to the lower, activated insulating layer and patterning the at least one upper insulating layer.

F | 25 (previously added). The process according to claim 24, which comprises patterning the lower insulating layer in the first working step.

26 (previously added). The process according to claim 24, which comprises choosing a selected layer from the group consisting of the at least upper one insulating layer and the lower insulating layer and patterning the selected layer after the selected layer has been applied.

27 (currently amended). A process for producing a component, which comprises:

in a first working step, applying a first insulating layer having a layer thickness between 0.05  $\mu\text{m}$  and 50 [0.05]  $\mu\text{m}$  to a substrate;

in a second working step, applying a second insulating layer having a layer thickness between 0.05  $\mu\text{m}$  and 50  $\mu\text{m}$  and being chemically different from said at least one lower insulating layer and patterning the second insulating layer; and

in a third working step, activating a layer selected from the group consisting of the first insulating layer and the second insulating layer.

28 (previously added). The process according to claim 27, which comprises patterning the first insulating layer in the first working step.

29 (previously added). The process according to claim 27, which comprises patterning the second insulating layer after the second working step and before the third working step.

30 (currently amended). The process according to claim 29, which comprises patterning the first [lower] insulating layer, after the first working step.

F/ 31 (currently amended). The process according to claim 27,  
which comprises patterning the first [lower] insulating layer,  
after the first working step.

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